Title (en)

PROCESS FOR FABRICATING A SILICON-BASED THIN-FILM PHOTOVOLTAIC CELL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER PHOTOVOLTAISCHEN DÜNNSCHICHTZELLE AUF SILIZIUMBASIS

Title (fr)

PROCEDE DE FABRICATION D'UNE CELLULE PHOTOVOLTAÏQUE A BASE DE SILICIUM EN COUCHES MINCES

Publication

EP 2281313 A2 20110209 (FR)

Application

EP 09738349 A 20090420

Priority

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Abstract (en)

[origin: WO2009133315A2] The invention relates to a process for fabricating a silicon-based thin-film photovoltaic cell. This fabrication process is characterized in that it includes a step a) of depositing a p-doped or n-doped amorphous silicon film, the X-ray diffraction spectrum of which has a line centred at 28° that has a mid-height width, denoted by a, such that 4.7° = a < 6.0° on a substrate (1). The invention is applicable in particular in the energy generation field.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

See references of WO 2009133315A3

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